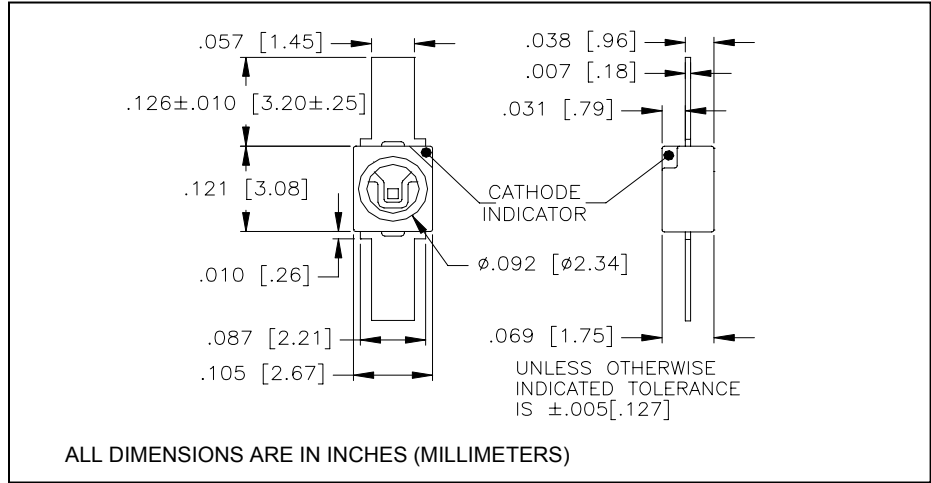


CLE100F

Gallium Arsenide IRED Flat Lead PLCC Package



August, 2001



features

- Flat lead PLCC package
- $\pm 60^\circ$ emission angle
- 940 nm peak wavelength

description

The CLE100F is a 940nm infrared emitting diode featuring current GaAs technology with a AlGaAs window for increased quantum efficiency. The chip is mounted in a compact, embedded leadframe package with flying lead configuration and overcoated with clear epoxy to provide a wide emission pattern. Different wavelength chips, different lenses and different lead configurations are available. For additional information, call Clairex.

absolute maximum ratings ($T_A = 25^\circ\text{C}$ unless otherwise stated)

storage temperature	-40°C to $+125^\circ\text{C}$
operating temperature	-40°C to $+125^\circ\text{C}$
lead soldering temperature ⁽¹⁾	240°C
maximum continuous current ⁽²⁾	30mA
peak forward current (10 μs pulse width, 100pps)	1A
maximum power dissipation ⁽³⁾	75mW
reverse voltage	5V

notes:

1. 0.06" (1.5mm) from case for 5 seconds maximum. Maximum temperature can be 260°C if reflow soldering.
2. Derate linearly 0.24mA/ $^\circ\text{C}$ from 25°C free air temperature to $T_A = +125^\circ\text{C}$.
3. Derate linearly 0.60mW/ $^\circ\text{C}$ from 25°C free air temperature to $T_A = +125^\circ\text{C}$.

electrical characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)						
symbol	parameter	min	typ	max	units	test conditions
P_O	Total power output ⁽⁴⁾	2.0	-	-	mW	$I_F = 20\text{mA}$
V_F	Forward voltage	-	-	1.5	V	$I_F = 20\text{mA}$
I_R	Reverse current	-	-	10	μA	$V_R = 5.0\text{V}$
λ_p	Peak emission wavelength	-	940	-	nm	$I_F = 20\text{mA}$
BW	Spectral bandwidth at half power points	-	50	-	nm	$I_F = 20\text{mA}$
θ_{HP}	Emission angle at half power points	-	120	-	deg.	$I_F = 20\text{mA}$

note: 4. Power output is measured in an integrating sphere.

Clairex reserves the right to make changes at any time to improve design and to provide the best possible

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